Product data sheet

1. General description

Dual enhanced ultrafast power diode in a SOT186A (TO-220AB) plastic package.

2. Features and benefits

- High thermal cycling performance
- Isolated package
- · Low thermal resistance
- Soft recovery characteristic minimizes power consuming oscillations
- · Very low on-state losses

3. Applications

- Dual mode (DCM and CCM) PFC
- · Power Factor Correction (PFC) for Interleaved Topology

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|------------------|-------------------------------------|---|-----|-----|-----|------|
| V_R | reverse voltage | DC | - | - | 600 | V |
| I _{FSM} | non-repetitive peak forward current | t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; SIN; per diode | - | - | 132 | A |
| | | t_p = 10 ms; $T_{j(init)}$ = 25 °C; SIN; per diode | - | - | 120 | А |
| Static charac | cteristics | | | | | |
| V _F | forward voltage | I _F = 10 A; T _j = 25 °C; <u>Fig. 4</u> | - | 1.4 | 2.1 | V |
| | | I _F = 10 A; T _j = 150 °C | - | 1.3 | 1.9 | V |
| Dynamic cha | aracteristics | | | | | |
| t _{rr} | reverse recovery time | $I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig. 5 | - | 20 | 35 | ns |

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5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------------------|----------------------------|----------------|
| 1 | A1 | anode 1 | mb | A1 |
| 2 | K | cathode | | A1 |
| 3 | A2 | anode 2 | | K sym125 |
| mb | n.c. | mounting base; isolated | 1 2 3 TO-220F (SOT186A) | |

6. Ordering information

Table 3. Ordering information

| Type number | Package | | | | |
|-------------|---------|---|---------|--|--|
| | Name | Description | Version | | |
| BYV410X-600 | TO-220F | plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack" | SOT186A | | |

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7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|--------------------|---------------------------------|--|-----|-----|------|
| V_{RRM} | repetitive peak reverse voltage | | - | 600 | V |
| V_{RWM} | crest working reverse voltage | | - | 600 | V |
| V_R | reverse voltage | DC | - | 600 | V |
| I _{O(AV)} | average output current | δ = 0.5 ; T _h \leq 42 °C; SQW; both diodes conducting; <u>Fig. 1</u> ; <u>Fig. 2</u> | - | 20 | Α |
| I _{FRM} | repetitive peak forward current | δ = 0.5 ; t_p = 25 $\mu s; T_h \leq $ 60 °C; SQW; per diode | - | 20 | Α |
| I _{FSM} | non-repetitive peak | t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; SIN; per diode | - | 132 | Α |
| | forward current | t _p = 10 ms; T _{j(init)} = 25 °C; SIN; per diode | - | 120 | Α |
| T _{stg} | storage temperature | | -40 | 150 | °C |
| T _j | junction temperature | | - | 150 | °C |

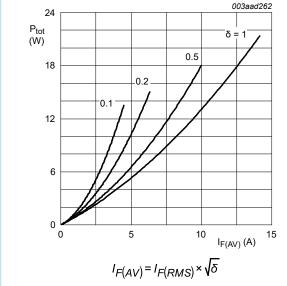


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

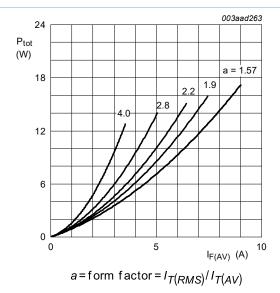


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

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8. Thermal characteristics

Table 5. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|----------------------|--|--|-----|-----|-----|------|
| R _{th(j-h)} | thermal resistance from junction to | with heatsink compound; per diode; Fig. 3 | - | - | 5 | K/W |
| | heatsink | with heatsink compound; both diodes conducting | - | - | 3 | K/W |
| $R_{\text{th(j-a)}}$ | thermal resistance from junction to ambient free air | | - | 55 | - | K/W |

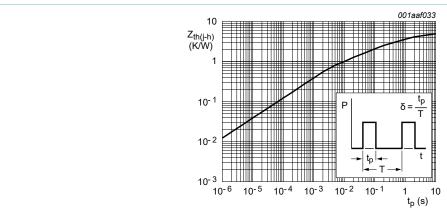


Fig. 3. Transient thermal impedance from junction to heatsink per diode as a function of pulse width

9. Isolation characteristics

Table 6. Isolation characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|------------------------|-----------------------|---|-----|-----|------|------|
| V _{isol(RMS)} | RMS isolation voltage | 50 Hz < f < 60 Hz; sinusoidal waveform; relative humidity < 65 %; clean and dust free; from all terminals to external heatsink | - | - | 2500 | V |
| C _{isol} | isolation capacitance | from cathode to external heatsink; f = 1 MHz | - | 10 | - | pF |

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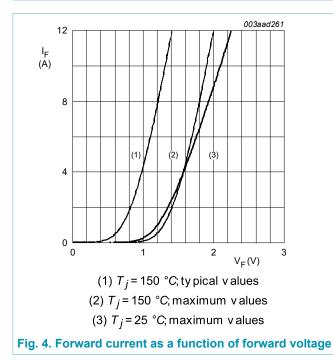
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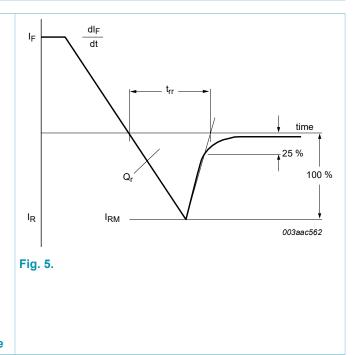
BYV410X-600

10. Characteristics

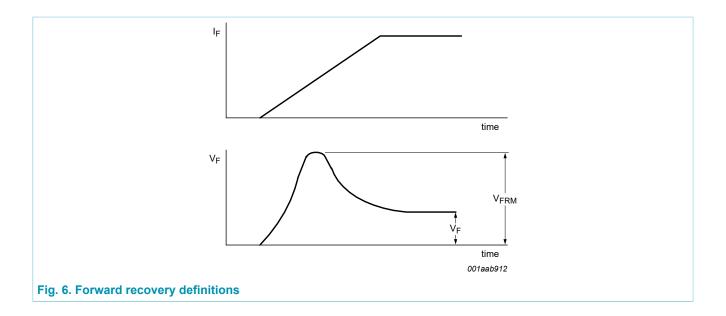
Table 7. Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------|-------------------------------|--|-----|-----|-----|------|
| Static chara | acteristics | | | | | |
| V _F | forward voltage | I _F = 10 A; T _j = 25 °C; <u>Fig. 4</u> | - | 1.4 | 2.1 | V |
| | | I _F = 10 A; T _j = 150 °C | - | 1.3 | 1.9 | V |
| I _R | reverse current | V _R = 600 V; T _j = 100 °C | - | 1 | 1.5 | mA |
| | | V _R = 600 V; T _j = 25 °C | - | 13 | 50 | μA |
| Dynamic ch | naracteristics | | | | | |
| t _{rr} | reverse recovery time | $I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 5$ | - | 20 | 35 | ns |
| I _{RM} | peak reverse recovery current | $I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; Fig. 5 | - | 1.4 | 1.9 | Α |
| Q _r | recovered charge | I _F = 1 A; V _R = 30 V; dI _F /dt = 100 A/μs | - | 15 | 28 | nC |
| V_{FR} | forward recovery voltage | I _F = 1 A; dI _F /dt = 100 A/µs; <u>Fig. 6</u> | - | 3.2 | - | V |



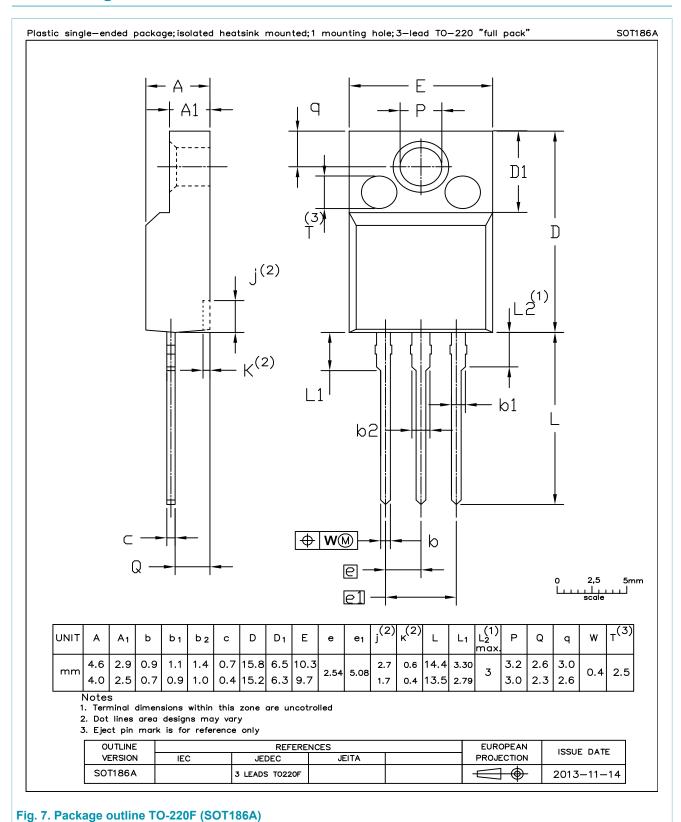


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11. Package outline



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12. Legal information

Data sheet status

| Document status [1][2] | Product status [3] | Definition |
|--------------------------------------|--------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
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| Product [short] data sheet | Production | This document contains the product specification. |

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